Abstracts

Far-Infrared Properties of Interacting Donors in Antimony-Doped Germanium

K. Yoshihiro, M. Tokumoto and C. Yamanouchi. "Far-Infrared Properties of Interacting Donors in Antimony-Doped Germanium." 1974 Transactions on Microwave Theory and Techniques 22.12 (Dec. 1974, Part I [T-MTT] (Special Issue on the Proceedings of the First International Conference on Submillimeter Waves and Their Applications)): 1072-1076.

Absorption and photoconductivity of 337-µm radiation in Sb-doped Ge with excess donor concentrations ranging from 1.2 x 10/sup 16/ to 3.6 x 10/sup 17/ cm/sup -3/ have been investigated at liquid-He temperatures. The result suggests the existence of a "delocalized" excited state between the conduction band and the donor ground state which arises from the overlapping of donor wave functions.

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